P1.1 AlGaN channel High Electron Mobility Transistors grown by NH3-MBE on Silicon substrates

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P1.3 AlScN alloys as pseudo-substrate for InGaN

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P1.5 Empirical Study of the Impact of Process Deviations on Structure and Performance of MIR-QCL for Volume Production

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P1.7 Fermi level control by above band gap illumination during molecular beam epitaxy growth of Mg-doped GaN

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P1.9 GaN/AlGaN quantum wells grown on high-quality GaN substrates in the perspective of indirect exciton diffusion

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P1.11 Growth and optimization of N-polar GaN epilayers on silicon substrates using ammonia-MBE and a hybrid NbN/AlN buffer layer

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P1.13 Growth of InAlN/NbN Heterostructures in Indium-rich Conditions by Plasma Assisted MBE

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P1.15 High Resolution Temperature Mapping of Intentionally Induced Thermal Gradients on GaSb Wafers during Growth

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P1.17 Influence of growth temperature and scandium concentration on the oxidation of ScAlN films grown by molecular beam epitaxy

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P1.19 Investigation of the effect of GaAs substrate orientations and doping on the electrical and optical properties of InGaP solar cell structures

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P1.21 Metal-Modulated Growth of Cubic, Red Emitting InGaN Layers and Self-Assembled InGaN/GaN Quantum Wells by Molecular Beam Epitaxy

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P1.23 Photoluminescence investigation of the annealing effects on GaAsBi quantum wells with parabolic AlGaAs barriers

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P1.25 Production of mm-Wave epiwafers of GaN on Si grown by NH3-MBE

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P1.27 Short wavelength infrared avalanche photodiode beyond 2.0 μm based on InGaAs/GaAsSb supperlattice as the absorber

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P1.29 Silicon epitaxy using trisilane

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P1.31 Automated growth of DBR supervised by in-situ spectral reflectance measurement

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P1.33 Key Points of Compound Semiconductor Material Evaluation by High resolution XRD

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P1.35 Manufacturing of Three Terminal Heterojunction Bipolar Solar Cells based on AlGaAs grown by MBE

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P1.37 NIR Diode Emitters for Applications in Biophotonics

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P1.39 Progress towards closed cycle AI controlled MBE systems

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P1.41 Growth and optical properties of $Al_{1-x}Ga_xAs0.56Sb0.44$ on InGaAs/InP

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P1.43 In-situ measurement of AlAs growth rate by magnification inferred curvature method

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P1.45 In situ control of GaN growth rate in nitrogen limited regime

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